



General Description

The ZM027N03N combines advanced trench MOSFET technology with a low resistance package to provide extremely low R_DS(ON) . This device is ideal for load switch and battery protection applications.

Features

Advance high cell density Trench technology
DS(ON) to minimize conductive loss

Application

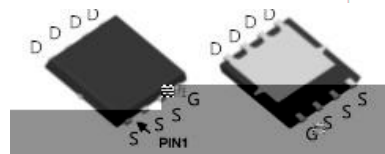
nd Synchronous Rectifier

Product Summary



4

2



Ordering Information:

Table with 2 columns and 4 rows containing ordering information like quantity and reel tape details.

Absolute Maximum Ratings TC =25

Table with 4 columns: Parameter, Symbol, Rating, Unit. Lists various electrical ratings for the MOSFET.





Fig.7 Switching Time Measurement Circuit

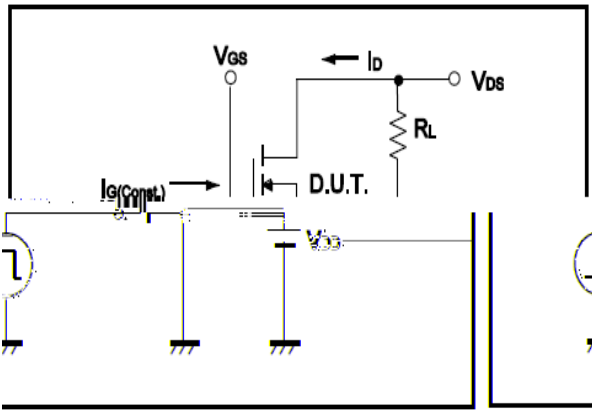


Fig.8 Gate Charge Waveform

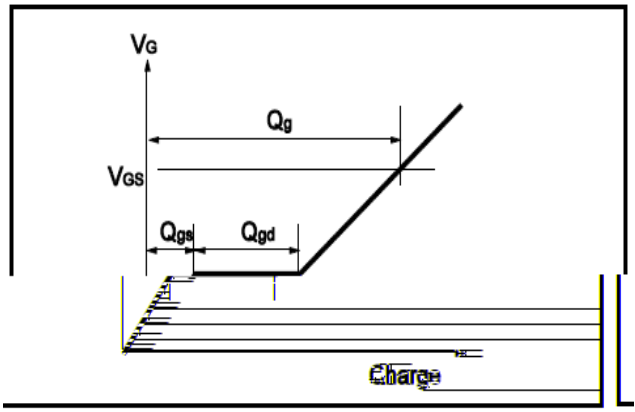


Fig.9 Switching Time Measurement Circuit

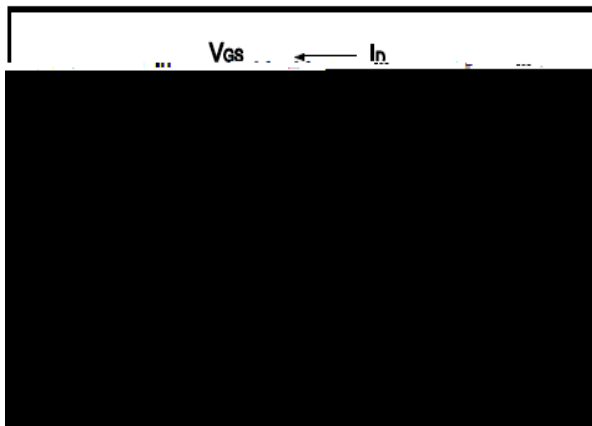


Fig.10 Gate Charge Waveform

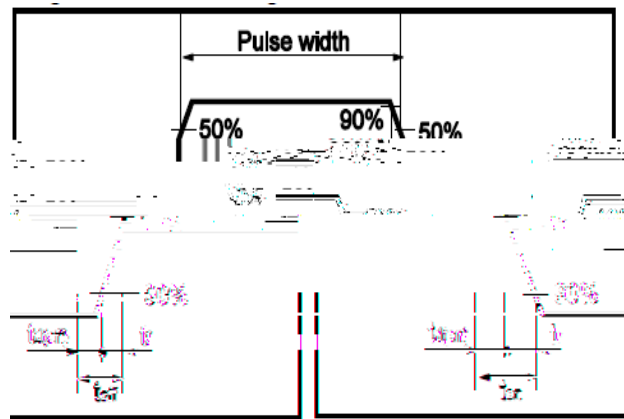


Fig.11 Avalanche Measurement Circuit

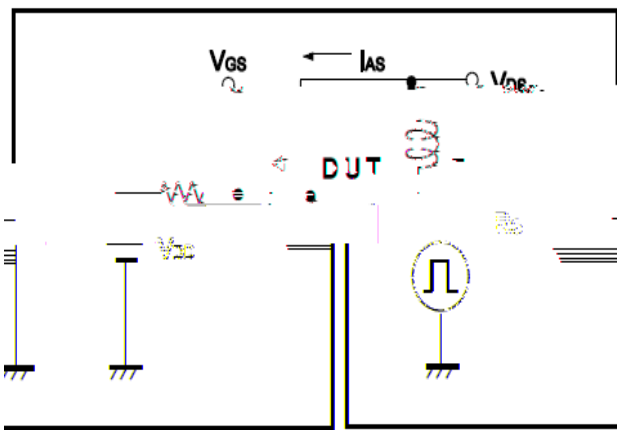
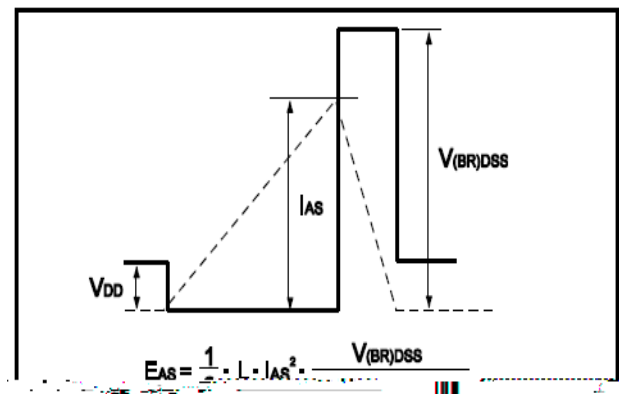


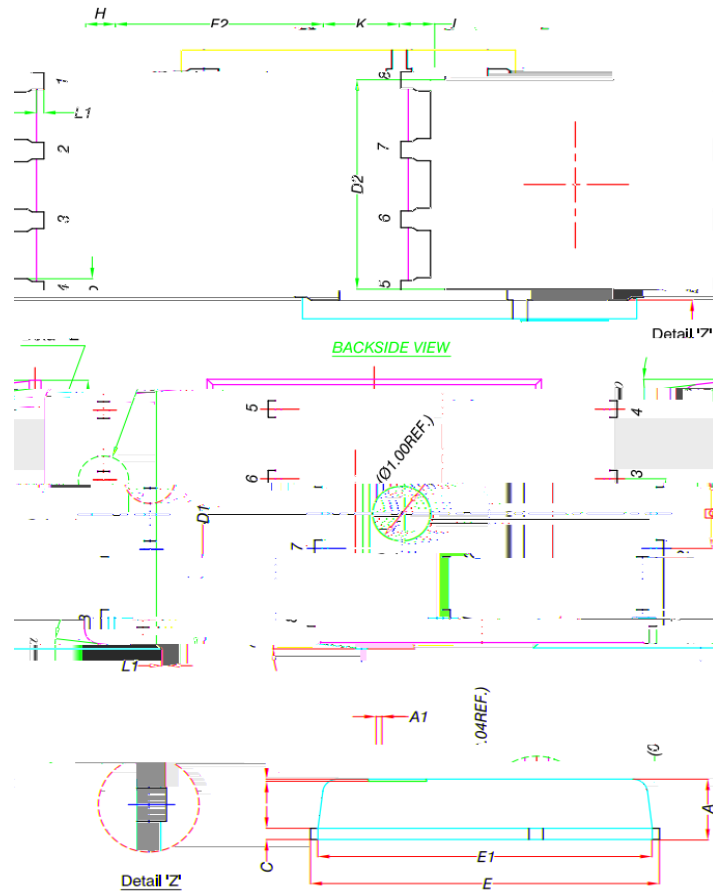
Fig.12 Avalanche Waveform





Dimensions DFN5x6

Unit mm



DIM.	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0	-	0.05
b	0.33	0.41	0.51
C	0.20	0.25	0.30
D1	4.80	4.90	5.00
D2	3.61	3.81	3.96

